

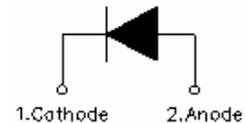
MBR20150 SCHOTTKY RECTIFIER

Applications:

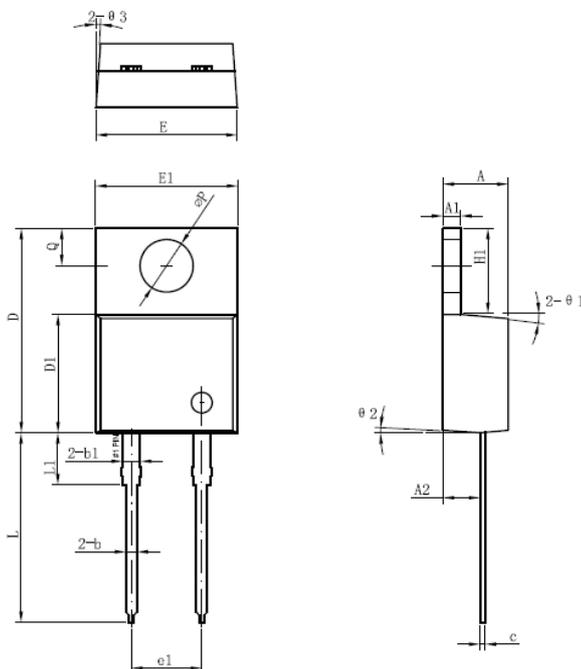
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Dimensions: In Inches / mm



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.64	14.94	15.24
D1	8.55	8.07	8.85
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1		5.08	
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1		3.80	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Q1		5°	
Q2		4°	
Q3		4°	

TO-220AC



Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
B = Package type
20 = Forward Current (20A)
150 = Reverse Voltage (150V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR20150	TO-220AC (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C=110^{\circ}C$, rectangular wave form	20	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	250	A



Electrical Characteristics:

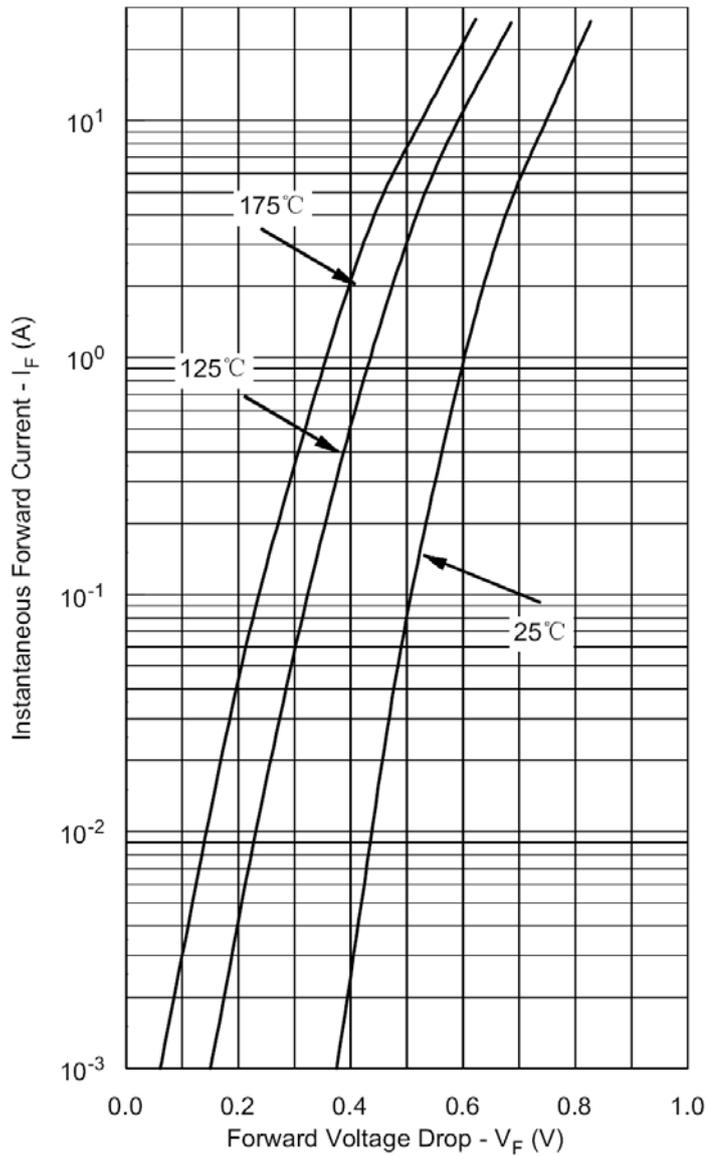
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 20A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.95	V
	V_{F2}	@ 20 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.92	V
Max. Reverse Current at DC condition	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
Max. Reverse Current *	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	15.0	mA
Non-Repetitive Avalanche Energy	E_{AS}	$T_J = 25\text{ }^\circ\text{C}$, $I_{AS} = 2\text{ A}$, $L = 1\text{ mH}$	2	mJ
Max. Junction Capacitance	C_T	@ $V_R = 5\text{ V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$	900	pF
Typical Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

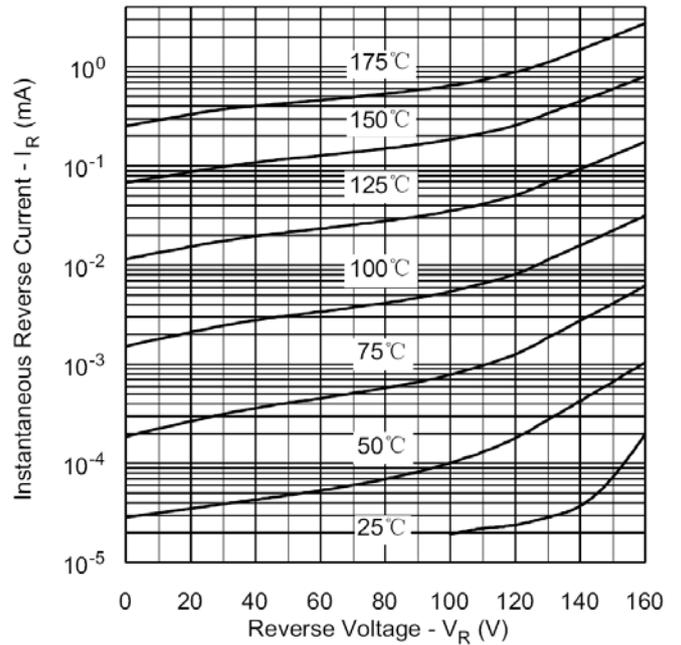
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	3.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	1.6	g
Case Style	TO-220AC			

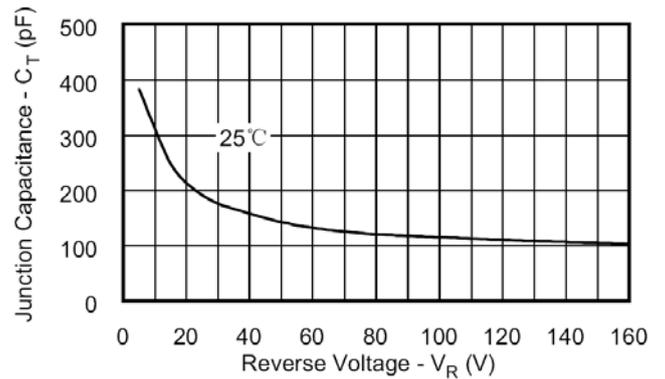
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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